Kazumasa Hiramatsu

List of Publications by Year
in descending order

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183	8,106	94433	49909
papers	citations	37 h-index	87 g-index

184	184	184	3589
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	P-Type Conduction in Mg-Doped GaN Treated with Low-Energy Electron Beam Irradiation (LEEBI). Japanese Journal of Applied Physics, 1989, 28, L2112-L2114.	1.5	1,754
2	Effects of ain buffer layer on crystallographic structure and on electrical and optical properties of GaN and Ga1â^'xAlxN (0 < x â‰¦ 0.4) films grown on sapphire substrate by MOVPE. Journal of Crystal Growth, 1989, 98, 209-219.	1.5	689
3	Fabrication and characterization of low defect density GaN using facet-controlled epitaxial lateral overgrowth (FACELO). Journal of Crystal Growth, 2000, 221, 316-326.	1.5	396
4	Selective growth of wurtzite GaN and AlxGa1â^'xN on GaN/sapphire substrates by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 1994, 144, 133-140.	1.5	312
5	Effects of the buffer layer in metalorganic vapour phase epitaxy of GaN on sapphire substrate. Thin Solid Films, 1988, 163, 415-420.	1.8	263
6	Relaxation Process of the Thermal Strain in the GaN/Î±-Al2O3Heterostructure and Determination of the Intrinsic Lattice Constants of GaN Free from the Strain. Japanese Journal of Applied Physics, 1992, 31, L1454-L1456.	1.5	259
7	Photoluminescence of Mg-doped p-type GaN and electroluminescence of GaN p-n junction LED. Journal of Luminescence, 1991, 48-49, 666-670.	3.1	253
8	Preparation of high-quality AlN on sapphire by high-temperature face-to-face annealing. Journal of Crystal Growth, 2016, 456, 155-159.	1.5	231
9	Relaxation Mechanism of Thermal Stresses in the Heterostructure of GaN Grown on Sapphire by Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1993, 32, 1528-1533.	1.5	214
10	Growth and Luminescence Properties of Mgâ€Doped GaN Prepared by MOVPE. Journal of the Electrochemical Society, 1990, 137, 1639-1641.	2.9	209
11	Growth of single crystalline GaN film on Si substrate using 3C-SiC as an intermediate layer. Journal of Crystal Growth, 1991, 115, 634-638.	1.5	188
12	Growth of single crystal GaN substrate using hydride vapor phase epitaxy. Journal of Crystal Growth, 1990, 99, 381-384.	1.5	176
13	Fabrication of GaN Hexagonal Pyramids on Dot-Patterned GaN/Sapphire Substrates via Selective Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1995, 34, L1184-L1186.	1.5	171
14	Annealing of an AlN buffer layer in N₂â€“CO for growth of a high-quality AlN film on sapphire. Applied Physics Express, 2016, 9, 025501.	2.4	166
15	Heteroepitaxial Growth and the Effect of Strain on the Luminescent Properties of GaN Films on ($11) Tj ETQq1 1 0.784314 rgBT /Ove	1.5	154
16	Effects of Reactor Pressure on Epitaxial Lateral Overgrowth of GaN via Low-Pressure Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1999, 38, L1000-L1002.	1.5	95
17	Preparation of AlxGa1-xN/GaN heterostructure by MOVPE. Journal of Crystal Growth, 1990, 104, 533-538.	1.5	93
18	Defect structure in selective area growth GaN pyramid on (111)Si substrate. Applied Physics Letters, 2000, 76, 2701-2703.	3.3	87

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19	Epitaxial lateral overgrowth techniques used in group III nitride epitaxy. Journal of Physics Condensed Matter, 2001, 13, 6961-6975.	1.8	86
20	Electron beam effects on blue luminescence of zinc-doped GaN. Journal of Luminescence, 1988, 40-41, 121-122.	3.1	84
21	Growth of Si-doped AlxGa1â€“xN on (0001) sapphire substrate by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 1991, 115, 648-651.	1.5	75
22	Sharp band edge photoluminescence of high-purity CuInS2 single crystals. Applied Physics Letters, 2001, 78, 742-744.	3.3	75
23	Raman Scattering Spectroscopy of Residual Stresses in Epitaxial AlN Films. Applied Physics Express, 2011, 4, 031001.	2.4	66
24	Selective Area Growth of GaN on Si Substrate Using SiO 2 Mask by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1998, 37, L966-L969.	1.5	63
25	Optical and Crystalline Properties of Epitaxial-Lateral-Overgrown-GaN Using Tungsten Mask by Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1999, 38, L356-L359.	1.5	60
26	Formation of GaN Self-Organized Nanotips by Reactive Ion Etching. Japanese Journal of Applied Physics, 2001, 40, L1301-L1304.	1.5	59
27	The formation of crystalline defects and crystal growth mechanism in InxGa1â^'xN/GaN heterostructure grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 1998, 189-190, 24-28.	1.5	58
28	Fabrication of Deep-Ultraviolet-Light-Source Tube Using Si-Doped AlGaN. Applied Physics Express, 2011, 4, 042103.	2.4	58
29	Metalorganic vapor phase epitaxy growth of (InxGa1-xN/GaN)n layered structures and reduction of indium droplets. Journal of Crystal Growth, 1994, 145, 209-213.	1.5	57
30	MOVPE growth of GaN on a misoriented sapphire substrate. Journal of Crystal Growth, 1991, 107, 509-512.	1.5	53
31	Metalorganic Vapor Phase Epitaxy of Thick InGaN on Sapphire Substrate. Japanese Journal of Applied Physics, 1997, 36, 3381-3384.	1.5	51
32	Impact of high-temperature annealing of AlN layer on sapphire and its thermodynamic principle. Japanese Journal of Applied Physics, 2016, 55, 05FL02.	1.5	48
33	Cross-sectional TEM study of microstructures in MOVPE GaN films grown on Î±-Al2O3 with a buffer layer of AlN. Journal of Crystal Growth, 1991, 115, 381-387.	1.5	45
34	Dependence of internal quantum efficiency on doping region and Si concentration in Al-rich AlGaN quantum wells. Applied Physics Letters, 2012, 101, 042110.	3.3	45
35	The Composition Pulling Effect in InGaN Growth on the GaN and AlGaN Epitaxial Layers Grown by MOVPE. Materials Research Society Symposia Proceedings, 1996, 449, 89.	0.1	43
36	Hydride vapor-phase epitaxy growth of high-quality GaN bulk single crystal by epitaxial lateral overgrowth. Journal of Crystal Growth, 1998, 189-190, 67-71.	1.5	42

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37	Effect of thermal annealing on AlN films grown on sputtered AlN templates by metalorganic vapor phase epitaxy. Japanese Journal of Applied Physics, 2018, 57, 01AD05.	1.5	41
38	MOVPE growth of thick homogeneous InGaN directly on sapphire substrate using AlN buffer layer. Solid-State Electronics, 1997, 41, 145-147.	1.4	39
39	Growth of Thick AlN Layer by Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2005, 44, L505-L507.	1.5	37
40	A study on barrier height of Auî—ĄlxGa1 â^' xN Schottky diodes in the range 0 â‰¤ x â‰¤ 0.20. Solid-State Electronics, 1997, 41, 287-294.	1.4	36
41	Selective Area Growth of GaN Using Tungsten Mask by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 1998, 37, L845-L848.	1.5	36
42	Transmission Electron Microscopy Investigation of Dislocations in GaN Layer Grown by Facet-Controlled Epitaxial Lateral Overgrowth. Japanese Journal of Applied Physics, 2001, 40, L309-L312.	1.5	34
43	The initial stage of LPE growth of InGaAsP on GaAs in the region of immiscibility. Journal of Crystal Growth, 1986, 79, 978-983.	1.5	33
44	Growth and Characterization of AlGaN Multiple Quantum Wells for Electron-Beam Target for Deep-Ultraviolet Light Sources. Japanese Journal of Applied Physics, 2013, 52, 01AF03.	1.5	28
45	High-quality AlN growth on 6H-SiC substrate using three dimensional nucleation by low-pressure hydride vapor phase epitaxy. Japanese Journal of Applied Physics, 2014, 53, 05FL03.	1.5	26
46	AlN homoepitaxial growth on sublimation-AlN substrate by low-pressure HVPE. Journal of Crystal Growth, 2012, 350, 69-71.	1.5	24
47	Effects of initial stages on the crystal quality of nonpolar a-plane AlN on r-plane sapphire by low-pressure HVPE. Journal of Crystal Growth, 2009, 311, 3801-3805.	1.5	23
48	Growth of High-Quality Si-Doped AlGaN by Low-Pressure Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 095502.	1.5	23
49	Fabrication of high-crystallinity a-plane AlN films grown on r-plane sapphire substrates by modulating buffer-layer growth temperature and thermal annealing conditions. Journal of Crystal Growth, 2017, 468, 845-850.	1.5	23
50	Influence of off-cut angle of r-plane sapphire on the crystal quality of nonpolar a-plane AlN by LP-HVPE. Journal of Crystal Growth, 2009, 311, 4473-4477.	1.5	22
51	Inhomogeneous distribution of defect-related emission in Si-doped AlGaN epitaxial layers with different Al content and Si concentration. Journal of Applied Physics, 2014, 115, .	2.5	21
52	Sub-micron fine structure of GaN by metalorganic vapor phase epitaxy (MOVPE) selective area growth (SAG) and buried structure by epitaxial lateral overgrowth (ELO). Journal of Crystal Growth, 1998, 189-190, 78-82.	1.5	20
53	Crystal Orientation Fluctuation of Epitaxial-Lateral-Overgrown GaN with W Mask and SiO2 Mask Observed by Transmission Electron Diffraction and X-Ray Rocking Curves. Japanese Journal of Applied Physics, 1999, 38, L1299-L1302.	1.5	20
54	Photoluminescence study of Si-doped a-plane GaN grown by MOVPE. Journal of Crystal Growth, 2009, 311, 2906-2909.	1.5	20

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55	Nitridating r-plane sapphire to improve crystal qualities and surface morphologies of a-plane GaN grown by metalorganic vapor phase epitaxy. Applied Physics Letters, 2009, 95, .	3.3	20
56	MOVPE growth of GaN on Si substrate with 3C-SiC buffer layer. Japanese Journal of Applied Physics, 2014, 53, 05FL09.	1.5	20
57	Selective area growth and epitaxial lateral overgrowth of GaN by metalorganic vapor phase epitaxy and hydride vapor phase epitaxy. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 1999, 59, 104-111.	3.5	19
58	Extraordinary Optical Transmission Exhibited by Surface Plasmon Polaritons in a Double-Layer Wire Grid Polarizer. Plasmonics, 2015, 10, 1657-1662.	3.4	19
59	Structural and electrical properties of Si-doped a-plane GaN grown on r-plane sapphire by MOVPE. Journal of Crystal Growth, 2009, 311, 2899-2902.	1.5	18
60	Facets Formation Mechanism of GaN Hexagonal Pyramids on Dot-Patterns via Selective MOVPE. Materials Research Society Symposia Proceedings, 1995, 395, 267.	0.1	17
61	LPE Growth and Surface Morphology of InxGa1-xAsyP1-y(yâ‰0.01) on (100) GaAs. Japanese Journal of Applied Physics, 1984, 23, 68-73.	1.5	16
62	Characterization of GaN-Based Schottky Barrier Ultraviolet (UV) Detectors in the UV and Vacuum Ultraviolet (VUV) Region Using Synchrotron Radiation. Japanese Journal of Applied Physics, 2001, 40, L368-L370.	1.5	16
63	Suppression of Crack Generation Using High-Compressive-Strain AlN/Sapphire Template for Hydride Vapor Phase Epitaxy of Thick AlN Film. Japanese Journal of Applied Physics, 2007, 46, L552-L555.	1.5	16
64	Effects of Substrate Plane on the Growth of High Quality AlN by Hydride Vapor Phase Epitaxy. Applied Physics Express, 2009, 2, 111004.	2.4	16
65	Control of AlN buffer/sapphire substrate interface for AlN growth. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2069-2071.	0.8	16
66	Influence of growth interruption and Si doping on the structural and optical properties of AlxGaN/AlN (x>0.5) multiple quantum wells. Journal of Crystal Growth, 2007, 298, 500-503.	1.5	15
67	Influence of growth conditions on Al incorporation to AlxGa1â^'xN (x>0.4) grown by MOVPE. Journal of Crystal Growth, 2007, 298, 372-374.	1.5	14
68	Silicon concentration dependence of optical polarization in AlGaN epitaxial layers. Applied Physics Letters, 2011, 98, .	3.3	14
69	Effects of carrier gas ratio and growth temperature on MOVPE growth of AlN. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 499-502.	0.8	14
70	Raman Scattering of InGaAsP Lattice-Matched to GaAs in the Region of Immiscibility. Japanese Journal of Applied Physics, 1993, 32, 2718-2721.	1.5	13
71	Antireflection Effect of Self-Organized GaN Nanotip Structure from Ultraviolet to Visible Region. Japanese Journal of Applied Physics, 2002, 41, L1134-L1136.	1.5	13
72	Orientation dependence of polarized Raman spectroscopy for nonpolar, semi-polar, and polar bulk GaN substrates. Applied Physics Letters, 2012, 100, .	3.3	13

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73	AlN Grown ona- andn-Plane Sapphire Substrates by Low-Pressure Hydride Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JB31.	1.5	13
74	Fabrication of Binary Diffractive Lenses and the Application to LED Lighting for Controlling Luminosity Distribution. Optics and Photonics Journal, 2013, 03, 67-73.	0.4	13
75	Using surface-plasmon polariton at the GaP-Au interface in order to detect chemical species in high-refractive-index media. Optics Communications, 2015, 341, 64-68.	2.1	13
76	Effects of AlN buffer layer thickness on the crystallinity and surface morphology of 10-Âµm-thicka-plane AlN films grown onr-plane sapphire substrates. Applied Physics Express, 2016, 9, 081001.	2.4	13
77	Cathodoluminescence of MOVPE-grown GaN layer on Î±-Al2O3. Journal of Crystal Growth, 1990, 99, 375-380.	1.5	12
78	Excitation mechanism of surface plasmon polaritons in a double-layer wire grid structure. Applied Physics A: Materials Science and Processing, 2017, 123, 1.	2.3	12
79	Fabrication of perfect plasmonic absorbers for blue and near-ultraviolet lights using double-layer wire-grid structures. Journal of the European Optical Society-Rapid Publications, 2021, 17, .	1.9	12
80	Gradual tilting of crystallographic orientation and configuration of dislocations in GaN selectively grown by vapour phase epitaxy methods. Journal of Electron Microscopy, 2000, 49, 331-338.	0.9	11
81	Metalorganic Vapor Phase Epitaxy Growth and Study of Stress in AlGaN Using Epitaxial AlN as Underlying Layer. Japanese Journal of Applied Physics, 2003, 42, L572-L574.	1.5	11
82	Deep Electronic Levels of Al_xGa_{1-x}N with a Wide Range of Al Composition Grown by Metalâ€“Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2010, 49, 101001.	1.5	11
83	HVPE growth of AlN on trenchâ€•patterned 6Hâ€SiC substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 467-469.	0.8	11
84	Analysis of Compositional Variation at Initial Transient Time in LPE Growth of InGaAsP/GaAs System. Japanese Journal of Applied Physics, 1985, 24, 1030-1035.	1.5	10
85	Effect of lattice mismatch between epitaxial layer and substrate on immiscibility of InGaAsP/GaAs LPE layers. Journal of Crystal Growth, 1988, 87, 446-452.	1.5	10
86	Epitaxial lateral overgrowth of GaN on selected-area Si(111) substrate with nitrided Si mask. Journal of Crystal Growth, 2003, 248, 573-577.	1.5	10
87	In-plane structural anisotropy and polarized Raman-active mode studies of nonpolar AlN grown on 6H-SiC by low-pressure hydride vapor phase epitaxy. Journal of Crystal Growth, 2010, 312, 490-494.	1.5	10
88	Electron microscopy analysis of microstructure of postannealed aluminum nitride template. Applied Physics Express, 2016, 9, 065502.	2.4	10
89	Growth of High-Quality Si-Doped AlGaN by Low-Pressure Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2011, 50, 095502.	1.5	10
90	Growth of InGaP epitaxial layers by liquid phase electro-epitaxy. Journal of Crystal Growth, 1991, 115, 304-308.	1.5	9

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91	Blue emission from InGaN/GaN hexagonal pyramid structures. Superlattices and Microstructures, 2007, 41, 341-346.	3.1	9
92	Optical properties of MOVPE-grown a-plane GaN and AlGaN. Journal of Crystal Growth, 2009, 311, 2903-2905.	1.5	9
93	Observation of longitudinal-optic-phonon-plasmon-coupled mode in n-type AlGaN alloy films. Applied Physics Letters, 2011, 99, 251904.	3.3	9
94	Transient photoluminescence of aluminum-rich (Al,Ga)N low-dimensional structures. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 765-768.	1.8	9
95	In Situ Monitoring of GaN Reactive Ion Etching by Optical Emission Spectroscopy. Japanese Journal of Applied Physics, 2001, 40, L313-L315.	1.5	8
96	In-plane electric field induced by polarization and lateral photovoltaic effect in a-plane GaN. Applied Physics Letters, 2009, 94, .	3.3	8
97	Fabrication of a binary diffractive lens for controlling the luminous intensity distribution of LED light. Optical Review, 2009, 16, 455-457.	2.0	8
98	a -plane AlN and AlGaN growth on r -plane sapphire by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2107-2110.	0.8	8
99	HVPE growth of thick AlN on trench-patterned substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1483-1486.	0.8	8
100	Huge binding energy of localized biexcitons in Al-rich AlxGa1â^'xN ternary alloys. Applied Physics Letters, 2011, 98, 081907.	3.3	8
101	Photoluminescence due to Inelastic Biexciton Scattering from an Al$_{0.61}$Ga$_{0.39}$N Ternary Alloy Epitaxial Layer at Room Temperature. Applied Physics Express, 2012, 5, 072401.	2.4	8
102	Correlation between in-plane strain and optical polarization of Si-doped AlGaN epitaxial layers as a function of Al content and Si concentration. Journal of Applied Physics, 2012, 112, 033512.	2.5	8
103	Selective-area growth of GaN on non- and semi-polar bulk GaN substrates. Japanese Journal of Applied Physics, 2014, 53, 05FL04.	1.5	8
104	Binding energy of localized biexcitons in AlGaN-based quantum wells. Applied Physics Express, 2014, 7, 122101.	2.4	8
105	Effect of surface pretreatment of r-plane sapphire substrates on the crystal quality of a-plane AlN. Japanese Journal of Applied Physics, 2016, 55, 05FA12.	1.5	8
106	High-temperature photoluminescence and photoluminescence excitation spectroscopy of Al_{0.60}Ga_{0.40}N/Al_{0.70}Ga_{0.30}N multiple quantum wells. Applied Physics Express, 2017, 10, 021002.	2.4	8
107	Characterization of GaN based Schottky UV detectors in the vacuum UV (VUV) and the soft X-ray (SX) region (10â€“100 nm). Physica Status Solidi A, 2003, 200, 147-150.	1.7	7
108	Growth control of carbon nanotubes by plasma-enhanced chemical vapor deposition and reactive ion etching. Vacuum, 2006, 80, 798-801.	3.5	7

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109	Fabrication of crackâ€free thick AlN film on aâ€plane sapphire by lowâ€pressure HVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 576-579.	0.8	7
110	LPE growth of InGaP/InGaAsP multiple thin layers on (111)A GaAs substrates. Journal of Crystal Growth, 1989, 98, 653-658.	1.5	6
111	Effects of initial conditions and growth temperature on the properties of nonpolar a â€plane AlN grown by LPâ€HVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, S478.	0.8	6
112	Variation of Surface Potentials of Si-Doped Al_xGa_{1-x}N (0) Tj ETQq0 0 0 rgBT /Overlock 10 Tf 50 Physics Express, 2010, 3, 021004.	2.4	6
113	Study of High-Quality and Crack-Free GaN Growth on 3C-SiC/Separation by Implanted Oxygen (111). Japanese Journal of Applied Physics, 2010, 49, 041001.	1.5	6
114	HVPE growth of câ€plane AlN on aâ€plane sapphire using nitridation layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 470-472.	0.8	6
115	Recombination dynamics of localized excitons in AlxGa1-xN (0.37<x<0.81) ternary alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2133-2135.	0.8	6
116	Cathodoluminescence Study of Optical Inhomogeneity in Si-Doped AlGaN Epitaxial Layers Grown by Low-Pressure Metalorganic Vapor-Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JL07.	1.5	6
117	Realization of Maskless Epitaxial Lateral Overgrowth of GaN on 3C-SiC/Si Substrates. Japanese Journal of Applied Physics, 2013, 52, 08JB07.	1.5	6
118	Excitationâ€dependent carrier dynamics in Alâ€rich AlGaN layers and multiple quantum wells. Physica Status Solidi (B): Basic Research, 2015, 252, 1043-1049.	1.5	6
119	HVPE homoepitaxy on freestanding AlN substrate with trench pattern. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 334-337.	0.8	6
120	Microstructural analysis of an epitaxial AlN thick film/trench-patterned template by three-dimensional reciprocal lattice space mapping technique. Applied Physics Express, 2016, 9, 111001.	2.4	6
121	Characterization of Interface Instability in InGaAsP LPE Growth on GaAs by Fourier Analysis. Japanese Journal of Applied Physics, 1985, 24, 822-827.	1.5	5
122	Hydrogen and Nitrogen Ambient Effects on Epitaxial Lateral Overgrowth (ELO) of GaN Via Metalorganic Vapor-Phase Epitaxy (MOVPE). Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	5
123	Characterization of high-quality epitaxial AlN films grown by MOVPE. Materials Research Society Symposia Proceedings, 2001, 693, 774.	0.1	5
124	Fabrication of thick AlN film by low pressure hydride vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1479-1482.	0.8	5
125	Influence of Si doping on the optical and structural properties of InGaN films. Journal of Crystal Growth, 2006, 290, 374-378.	1.5	5
126	Evidence for moving of threading dislocations during the VPE growth in GaN thin layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1487-1490.	0.8	5

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127	Effects of Si doping in high-quality AlN grown by MOVPE on trench-patterned template. Journal of Crystal Growth, 2013, 370, 74-77.	1.5	5
128	Selective Area Growth of Semipolar (202Ì„1) and (202Ì„1Ì„) GaN Substrates by Metalorganic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2013, 52, 08JC06.	1.5	5
129	Si concentration dependence of structural inhomogeneities in Si-doped AlxGa1â^'xN/AlyGa1â^'yN multiple quantum well structures (xâ€‰=â€‰0.6) and its relationship with internal quantum efficiency. Journal of Applied Physics, 2014, 116, .	2.5	5
130	A verification of immiscibility in InGaAsP quaternary alloys. Journal of Crystal Growth, 1988, 92, 311-315.	1.5	4
131	Electron microscope study of modulated structures and heterointerfaces in LPE-grown GaInAsP layers lattice-matched on GaAs. Journal of Crystal Growth, 1989, 98, 82-89.	1.5	4
132	TEM Analysis of Threading Dislocations in ELO-GaN Grown with Controlled Facet Planes. Materials Research Society Symposia Proceedings, 2000, 639, 11591.	0.1	4
133	n-type conductivity control of AlGaN with high Al mole fraction. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1435-1438.	0.8	4
134	Study on the effects of AlN interlayer in thick GaN grown on 3C-SiC/Si substrates. Journal of Crystal Growth, 2013, 370, 254-258.	1.5	4
135	Temperature Dependence of Stokes Shifts of Excitons and Biexcitons in Al_{0.61}Ga_{0.39}N Epitaxial Layer. Physica Status Solidi (B): Basic Research, 2018, 255, 1700374.	1.5	4
136	Hydrogen and Nitrogen Ambient Effects on Epitaxial Lateral Overgrowth (ELO) of GaN VIA Metalorganic Vapor-Phase Epitaxy (Movpe). MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 118-123.	1.0	3
137	Enhanced emission efficiency of InGaN films with Si doping. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 1944-1948.	0.8	3
138	Anisotropic crystalline morphology of epitaxial thick AlN films grown on triangular-striped AlN/sapphire template. Physica Status Solidi (A) Applications and Materials Science, 2014, 211, 731-735.	1.8	3
139	Fabrication and characterization of a binary diffractive lens for controlling focal distribution. Applied Optics, 2020, 59, 742.	1.8	3
140	Selective Area Growth (SAG) and Epitaxial Lateral Overgrowth (Elo) of GaN Using Tungsten Mask. Materials Research Society Symposia Proceedings, 1998, 537, 1.	0.1	2
141	Selective Area Growth (SAG) and Epitaxial Lateral Overgrowth (ELO) of GaN using Tungsten Mask. MRS Internet Journal of Nitride Semiconductor Research, 1999, 4, 441-446.	1.0	2
142	Effects of buffer layers and advanced technologies on heteroepitaxy of GaN. , 2001, , 210-232.		2
143	Reduction of dislocation density in AlGaN with high AlN molar fraction by using a rugged AlN epilayer. Materials Research Society Symposia Proceedings, 2004, 831, 353.	0.1	2
144	Enhancement of blue emission from Mg-doped GaN activated at low temperature in O2/N2 mixture. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2750-2753.	0.8	2

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145	Surface thermal stability of free-standing GaN substrates. Japanese Journal of Applied Physics, 2016, 55, 01AC08.	1.5	2
146	Confinement-enhanced biexciton binding energy in AlGaN-based quantum wells. Applied Physics Express, 2017, 10, 051003.	2.4	2
147	Cathodoluminescence study on local high-energy emissions at dark spots in AlGaN/AlGaN multiple quantum wells. Japanese Journal of Applied Physics, 2018, 57, 060311.	1.5	2
148	Raman scattering study of the immiscible region in InGaAsP grown by LPE on (100) and (111) GaAs. Journal of Electronic Materials, 1996, 25, 695-699.	2.2	1
149	Fabrication of GaN with Buried Tungsten (W) Structures Using Epitaxial Lateral Overgrowth (ELO) via LP-MOVPE. Materials Research Society Symposia Proceedings, 1999, 595, 1.	0.1	1
150	Fabrication of GaN with Buried Tungsten (W) Structures Using Epitaxial Lateral Overgrowth (ELO) via LP-MOVPE. MRS Internet Journal of Nitride Semiconductor Research, 2000, 5, 62-68.	1.0	1
151	Review of Facet Controlled Epitaxial Lateral Overgrowth (FACELO) of GaN via Low Pressure Vapor Phase Epitaxy. Materials Research Society Symposia Proceedings, 2000, 639, 841.	0.1	1
152	Effect of Ge in Cl2 Plasma for Reactive Ion Etching of GaN. Materials Research Society Symposia Proceedings, 2001, 693, 174.	0.1	1
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